

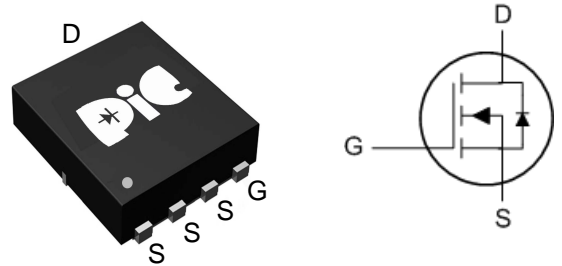
➤ General Description

This PAN80TV08V N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

➤ DFN3X3A-EP1



➤ Application

- DC/DC Primary Side Switch
- Industrial Synchronous
- Rectification Load Switch
- DC/DC Converters

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ¹	$I_D@T_C=25^\circ C$	50	A
Continuous Drain Current ¹	$I_D@T_C=100^\circ C$	32	A
Pulsed Drain Current ²	I_{DM}	150	A
Single Pulse Avalanche Energy ³	EAS	125	mJ
Avalanche Current	I_{AS}	50	A
Total Power Dissipation ⁴	$P_D@T_C=25^\circ C$	31	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ C$
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	65	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	4	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$	---	4.1	4.8	m Ω
		$V_{GS}=4.5V, I_D=12A$	---	4.5	5.4	
		$V_{GS}=2.5V, I_D=10A$	---	5.4	7.4	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.4	---	1.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=12A$	---	25	---	S
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.4	---	Ω
Total Gate Charge (4.5V)	Q_g	$V_{DS}=20V, V_{GS}=4.5V, I_D=12A$	---	31	---	nC
Gate-Source Charge	Q_{gs}		---	6.0	---	
Gate-Drain Charge	Q_{gd}		---	14	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, R_G=1.5\Omega$ $I_D=12A$	---	13	---	ns
Rise Time	T_r		---	46	---	
Turn-Off Delay Time	$T_{d(off)}$		---	32	---	
Fall Time	T_f		---	7.5	---	
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	3150	---	pF
Output Capacitance	C_{oss}		---	405	---	
Reverse Transfer Capacitance	C_{rss}		---	310	---	

➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5}	I_S	$V_G=V_D=0V, \text{ Force Current}$	---	---	50	A
Pulsed Source Current ^{2,5}	I_{SM}		---	---	150	A
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V

Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=50A$
4. Ensure that the channel temperature does not exceed $150^\circ C$.
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

➤ Typical Characteristics

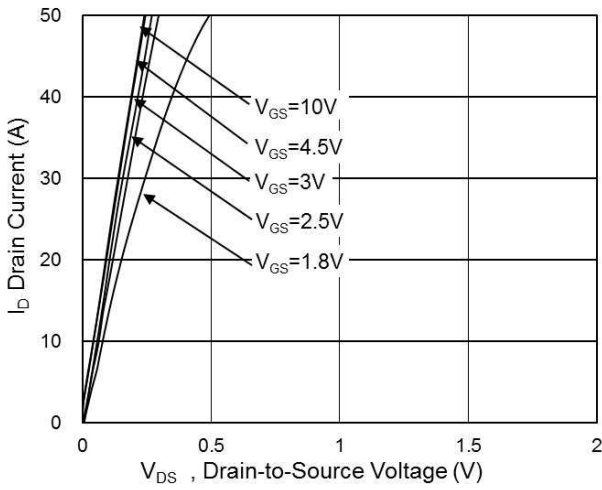


Fig.1 Typical Output Characteristics

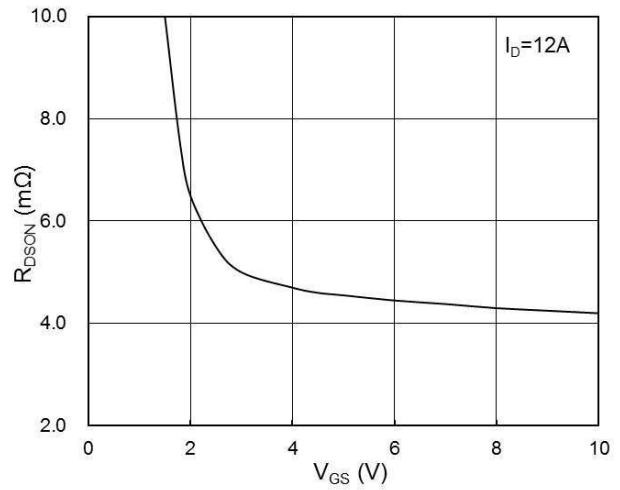


Fig.2 On-Resistance vs. G-S Voltage

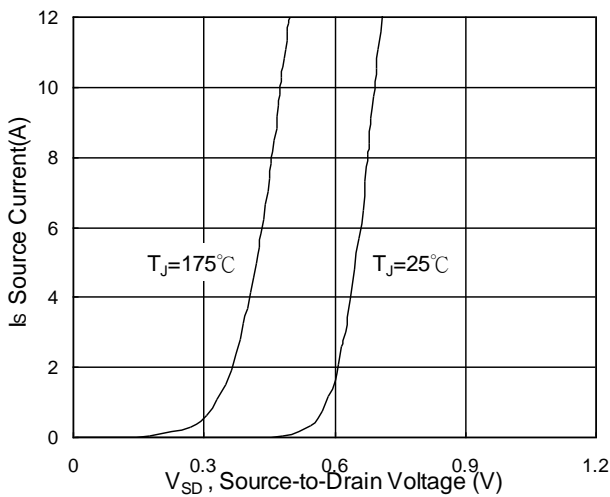


Fig.3 Forward Characteristics of Reverse

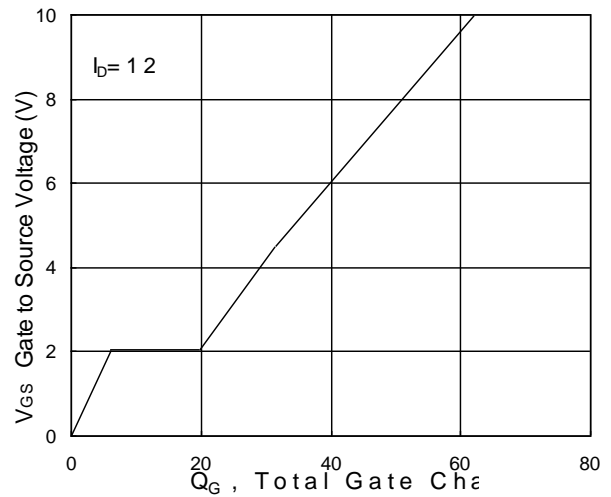


Fig.4 Gate-Charge Characteristics

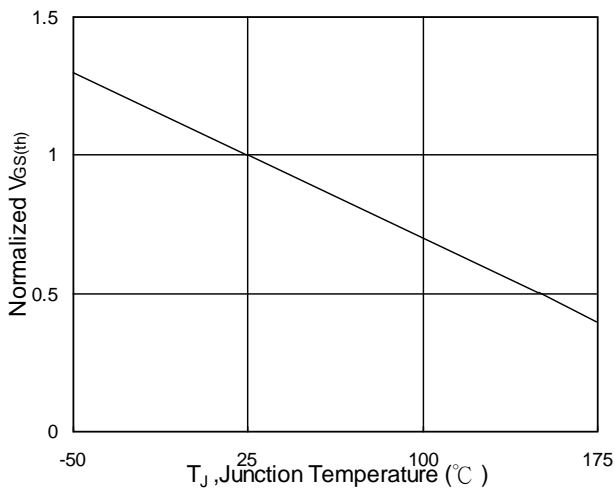


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

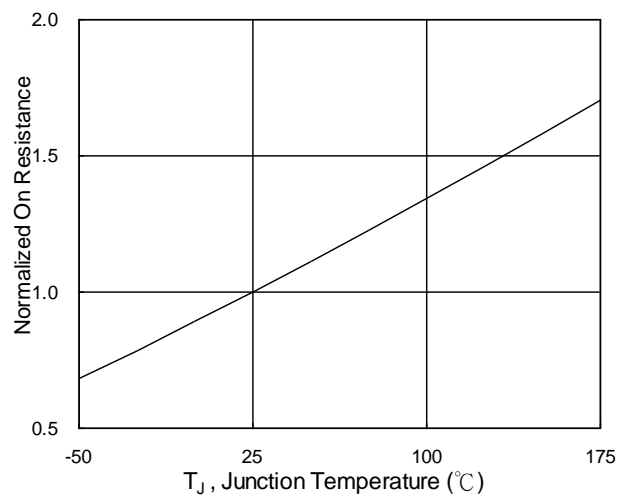


Fig.6 Normalized $R_{DS(ON)}$ vs. T_J

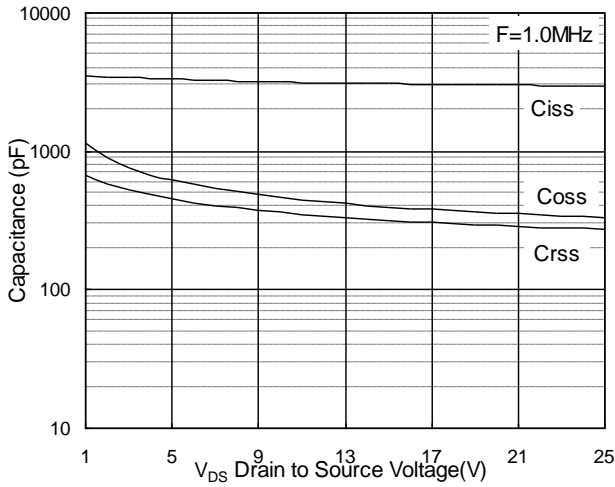


Fig.7 Capacitance

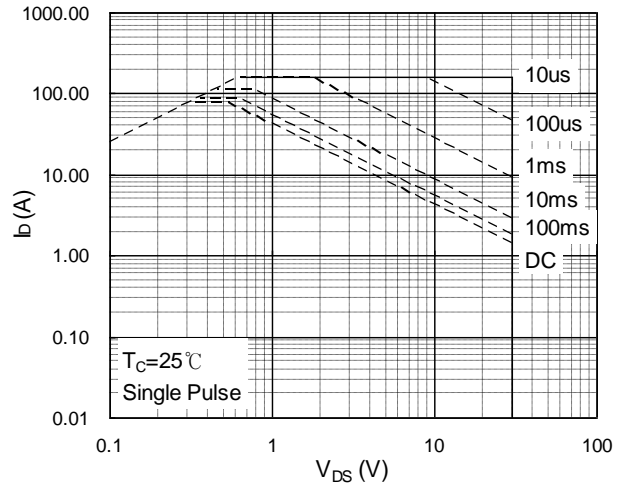


Fig.8 Safe Operating Area

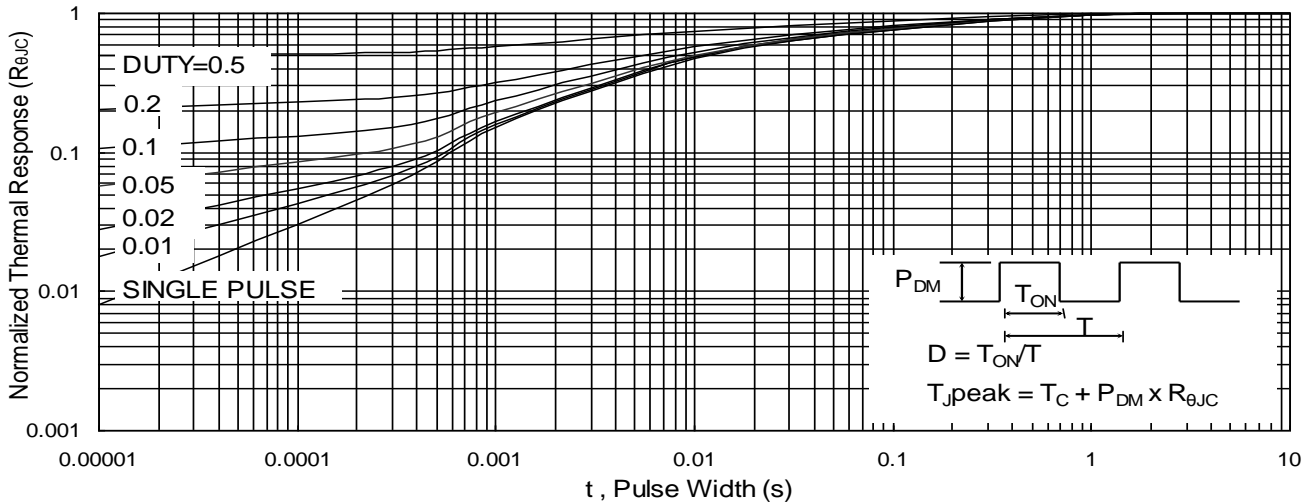


Fig.9 Normalized Maximum Transient Thermal Impedance

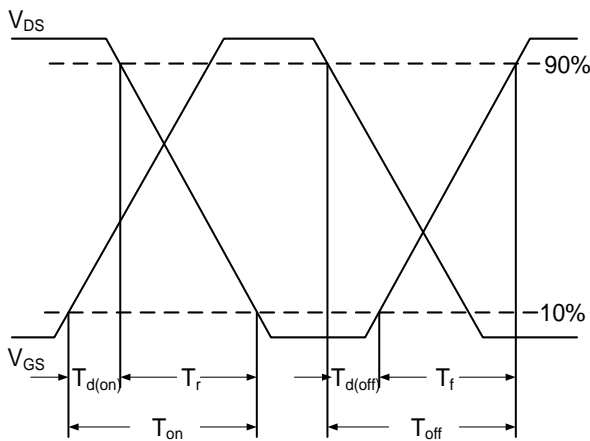


Fig.10 Switching Time Waveform

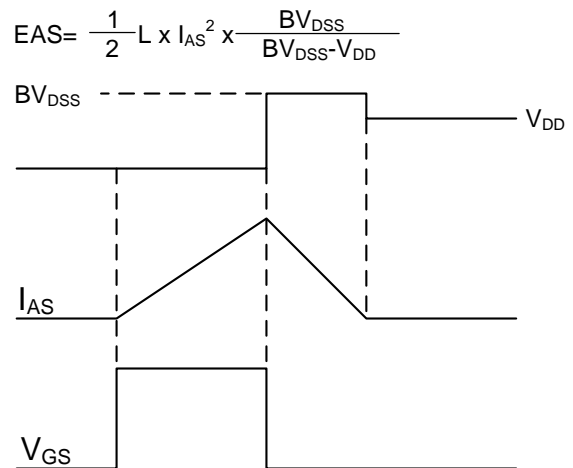
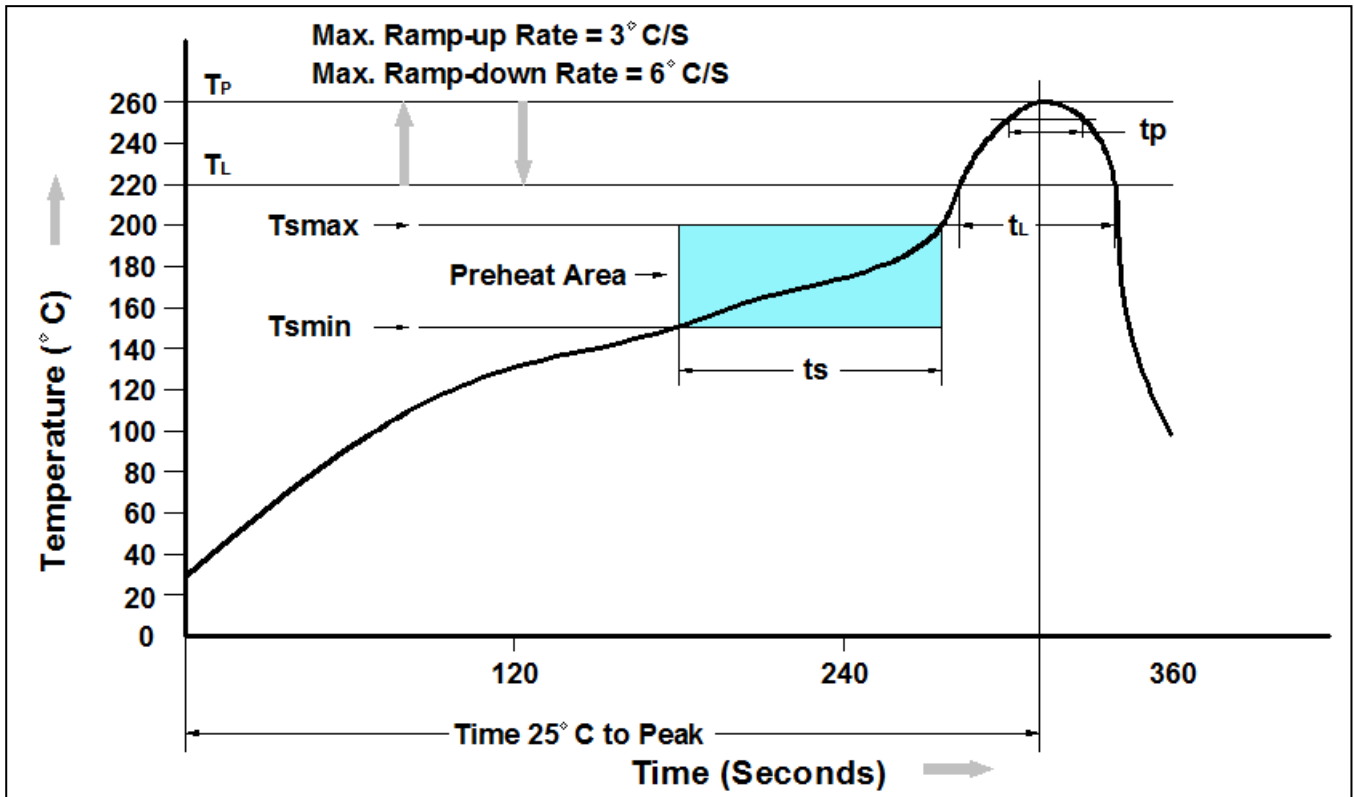


Fig.11 Unclamped Inductive Switching Waveform

➤ Recommand IR Reflow Soldering Thermal Profile

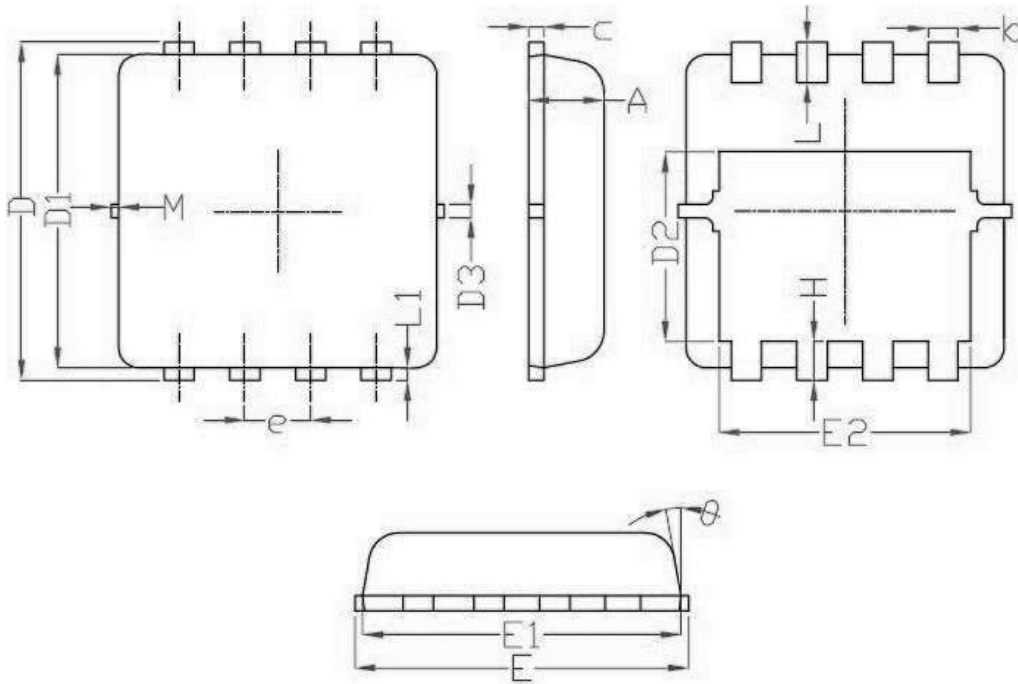


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN80TV08V	DFN3X3A-EP1 Reel	3000 pcs

➤ Package Information (DFN3X3A-EP1)



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.85	0.027	0.034
b	0.20	0.40	0.007	0.016
c	0.10	0.25	0.004	0.010
D	3.15	3.45	0.124	0.136
D1	2.90	3.20	0.114	0.126
D2	1.54	1.98	0.060	0.080
D3	0.10	0.30	0.004	0.012
E	3.15	3.45	0.124	0.136
E1	3.00	3.25	0.118	0.128
E2	2.29	2.65	0.090	0.104
e	0.65 BSC		0.025 BSC	
H	0.28	0.65	0.011	0.026
Θ	0°	14°	0°	14°
L	0.30	0.50	0.012	0.020
L1	0.13		0.005	
M	---	0.15	---	0.006

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